

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	0	((dummy sacrificial) near4 (layer film)) with interconnect\$4	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/27 14:05
S2	588	((dummy sacrificial) near4 (layer film)) with interconnect\$4	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/27 14:06
S3	18	((dummy sacrificial) near4 (layer film)) with interconnect\$4) with memory	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/27 14:09
S4	3733	438/622	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/27 14:09
S5	377	438/622 and (dummy sacrificial)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/27 14:09
S6	207	(438/622 and (dummy sacrificial)) and interconnect	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/27 16:46
S7	1	09/244788	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/27 15:34
S8	1	10/436921	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/27 16:19
S9	18	((438/622 and (dummy sacrificial)) and interconnect) and dish\$4	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/27 17:18
S10	0	10/629041	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/27 17:19

S11	0	"10629041"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/27 17:32
S12	4	"6492662"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/28 07:27
S13	28765	memory adj device.ti.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/28 07:27
S14	1639	(memory adj device.ti.) and trench	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/28 07:28
S15	11	((memory adj device.ti.) and trench) and phase adj change	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/28 07:29
S16	167	memory with phase adj change.ti.	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/28 18:05
S17	1	10/338646	US-PGPU B; USPAT; EPO; JPO	OR	ON	2004/09/28 18:06

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	122	(packag\$3 with terminal) with (signal near3 test\$4)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/08 15:08
L2	76	1 and voltage	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/08 15:09
L3	42	1 and (high with voltage)	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/08 15:45
L4	15	"6240535"	US-PGPU B; USPAT; EPO; JPO	OR	ON	2005/02/08 15:45